Preferred Devices

NPN Silicon Epitaxial Transistor

These NPN Silicon Epitaxial transistors are designed for use in audio amplifier applications. The device is housed in the SOT-223 package, which is designed for medium power surface mount applications.

- Pb–Free Package is Available
 High Current
 10
- The SOT-223 package can be soldered using wave or reflow. The formed leads absorb thermal stress during soldering, eliminating the possibility of damage to the die
- Available in 12 mm Tape and Reel Use BCP56T1 to order the 7 inch/1000 unit reel Use BCP56T3 to order the 13 inch/4000 unit reel
- PNP Complement is BCP53T1

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	80	Vdc
Collector-Base Voltage	V _{CBO}	100	Vdc
Emitter-Base Voltage	V _{EBO}	5	Vdc
Collector Current	I _C	1	Adc
Total Power Dissipation @ T _A = 25°C (Note 1) Derate above 25°C	P _D	1.5 12	Watts mW/°C
Operating and Storage Temperature Range	T _J , T _{stg}	-65 to 150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction-to-Ambient (surface mounted)	R _{θJA}	83.3	°C/W
Maximum Temperature for Soldering Purposes Time in Solder Bath	MID+	260 10	°C Sec

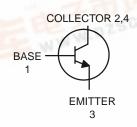
^{1.} Device mounted on a FR-4 glass epoxy printed circuit board 1.575 in x 1.575 in x 0.0625 in; mounting pad for the collector lead = 0.93 sq in.



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MEDIUM POWER NPN SILICON HIGH CURRENT TRANSISTOR **SURFACE MOUNT**





CASE 318E STYLE 1

MARKING DIAGRAM



= Specific Device Code

= Assembly Location

= Work Week

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characterist	ics	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Collector–Base Breakdown Voltage ($I_C = 100 \mu Adc, I_E = 0$)		V _{(BR)CBO}	100	_	_	Vdc
Collector–Emitter Breakdown Voltage (I _C = 1.0 mAdc, I _B = 0)		V _{(BR)CEO}	80	-	_	Vdc
Emitter–Base Breakdown Voltage $(I_E=10~\mu Adc,~I_C=0)$		V _{(BR)EBO}	5.0	-	_	Vdc
Collector–Base Cutoff Current (V _{CB} = 30 Vdc, I _E = 0)		Ісво	-	-	100	nAdc
Emitter-Base Cutoff Current (V _{EB} = 5.0 Vdc, I _C = 0)		I _{EBO}	-	-	10	μAdc
ON CHARACTERISTICS (Note 2)		•	•	•	•	•
DC Current Gain $ (I_C = 5.0 \text{ mA}, V_{CE} = 2.0 \text{ V}) $ $ (I_C = 150 \text{ mA}, V_{CE} = 2.0 \text{ V}) $ $ (I_C = 500 \text{ mA}, V_{CE} = 2.0 \text{ V}) $	All Part Types BCP56T1 BCP56-10T1 BCP56-16T1 All Types	h _{FE}	25 40 63 100 25	- - - -	_ 250 160 250 _	-
Collector–Emitter Saturation Voltage $(I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc})$		V _{CE(sat)}	-	-	0.5	Vdc
Base-Emitter On Voltage (I _C = 500 mAdc, V _{CE} = 2.0 Vdc)		V _{BE(on)}	-	-	1.0	Vdc
DYNAMIC CHARACTERISTICS						
Current–Gain – Bandwidth Product ($I_C = 10$ mAdc, $V_{CE} = 5.0$ Vdc, $f = 35$ M	lHz)	f _T	_	130	_	MHz

^{2.} Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
BCP56T1	ВН	SOT-223	1000 / Tape & Reel
BCP56T3	ВН	SOT-223	4000 / Tape & Reel
BCP56-10T1	BH-10	SOT-223	1000 / Tape & Reel
BCP56-16T1		SOT-223	1000 / Tape & Reel
BCP56-16T1G	BH-16	SOT-223 (Pb-Free)	1000 / Tape & Reel
BCP56-16T3		SOT-223	4000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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TYPICAL ELECTRICAL CHARACTERISTICS

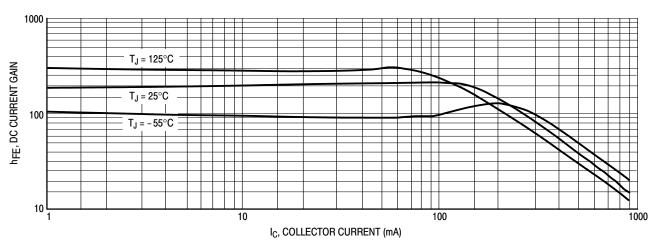


Figure 1. DC Current Gain

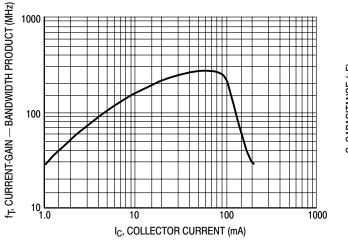


Figure 2. Current-Gain - Bandwidth Product

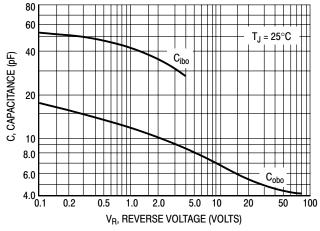


Figure 3. Capacitance

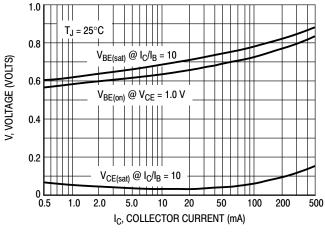


Figure 4. "On" Voltages

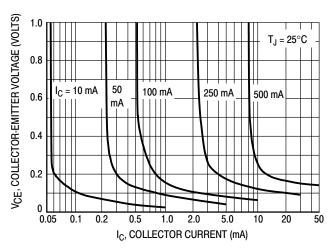
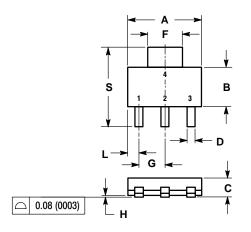
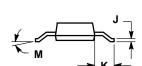


Figure 5. Collector Saturation Region

PACKAGE DIMENSIONS

SOT-223 (TO-261) CASE 318E-04 ISSUE K





NOTES:

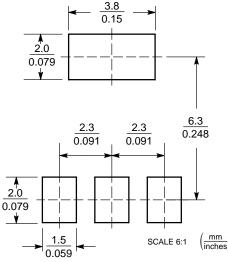
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.249	0.263	6.30	6.70	
В	0.130	0.145	3.30	3.70	
С	0.060	0.068	1.50	1.75	
D	0.024	0.035	0.60	0.89	
F	0.115	0.126	2.90	3.20	
G	0.087	0.094	2.20	2.40	
Н	0.0008	0.0040	0.020	0.100	
J	0.009	0.014	0.24	0.35	
K	0.060	0.078	1.50	2.00	
L	0.033	0.041	0.85	1.05	
M	0 °	10 °	0 °	10 °	
S	0.264	0.287	6.70	7.30	

PIN 1

- BASE COLLECTOR
- **EMITTER**
- COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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